

**2SC5597**

## Silicon NPN triple diffusion mesa type

For horizontal deflection output

## ■ Features

- High breakdown voltage, and high reliability through the use of a glass passivation layer
- High-speed switching
- Wide safe operation area

### ■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

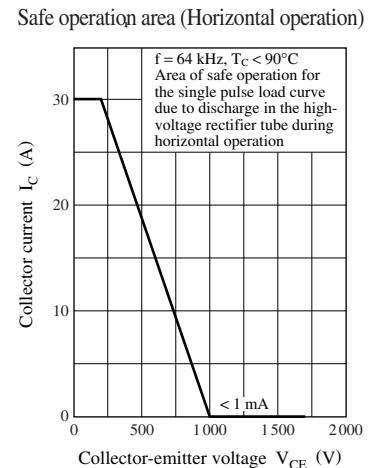
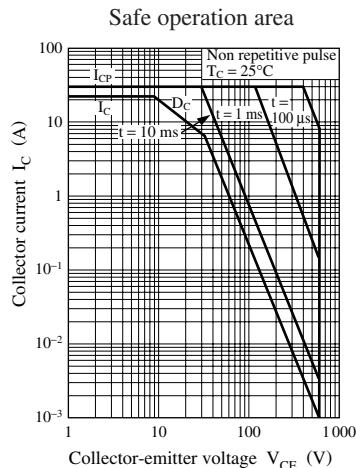
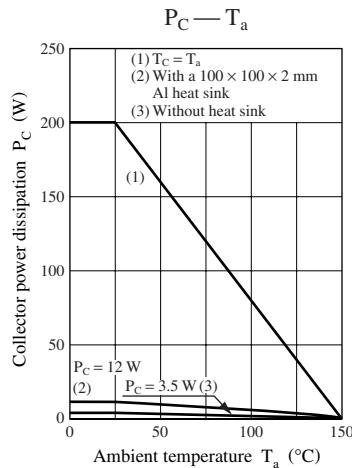
Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	1700	V
Collector-emitter voltage (E-B short)	$V_{CES}$	1700	V
Collector-emitter voltage (Base open)	$V_{CEO}$	600	V
Emitter-base voltage (Collector open)	$V_{EBO}$	7	V
Base current	$I_B$	11	A
Collector current	$I_C$	22	A
Peak collector current *	$I_{CP}$	30	A
Collector power dissipation	$P_C$	200	W
		3.5	
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

Note) \*: Non-repetitive peak collector current

## ■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 1\,000\text{ V}$ , $I_E = 0$			50	$\mu\text{A}$
		$V_{CB} = 1\,700\text{ V}$ , $I_E = 0$			1	$\text{mA}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 7\text{ V}$ , $I_C = 0$			50	$\mu\text{A}$
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 5\text{ V}$ , $I_C = 11\text{ A}$	6		12	—
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = 11\text{ A}$ , $I_B = 2.75\text{ A}$			3	$\text{V}$
Base-emitter saturation voltage	$V_{BE(\text{sat})}$	$I_C = 11\text{ A}$ , $I_B = 2.75\text{ A}$			1.5	$\text{V}$
Transition frequency	$f_T$	$V_{CE} = 10\text{ V}$ , $I_C = 0.1\text{ A}$ , $f = 0.5\text{ MHz}$		3		$\text{MHz}$
Storage time	$t_{\text{stg}}$	$I_C = 11\text{ A}$ , Resistance loaded			3.0	$\mu\text{s}$
Fall time	$t_f$	$I_{B1} = 2.75\text{ A}$ , $I_{B2} = -5.5\text{ A}$			0.2	$\mu\text{s}$

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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